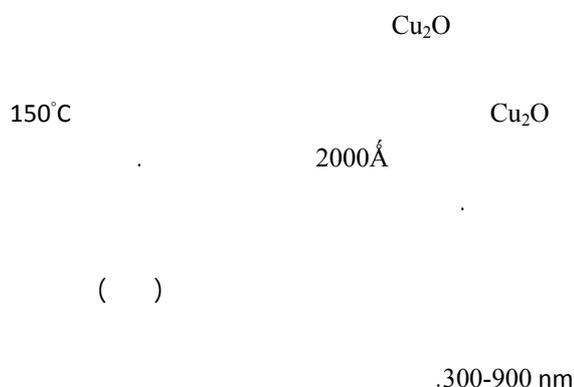




Cu₂O



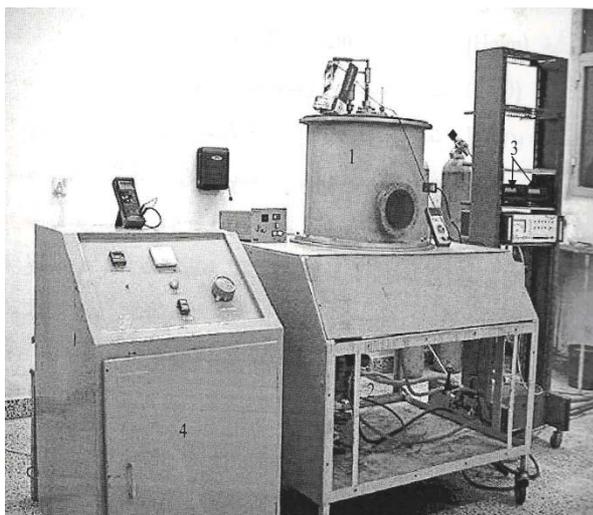
STUDYING OF THERMAL ANNEALING EFFECT ON STRUCTURAL AND OPTICAL PROPERTIES OF CU₂O THIN FILMS PREPARED BY PLASMA SPUTTERING METHOD

A.M.Sangery, A.S.Seerber, A.H.Dawood, S.Z.Abbas, H.K.Khalaf

Department of plasma, office of chemistry & materials physics,
Ministry of science and technology. Baghdad – Iraq.

Abstract

In this study we prepare Cu₂O films by using plasma sputtering method on substrate from glass type Pyrex; we used system of dipole sputtering with magnetic field. We studied the optical and structural properties to Cu₂O and we studied thermal annealing with 150°C on optical and structural properties for prepared thin films with thickness 2000Å for one hour. It showed that the thermal annealing leads to increase of optical energy gap. We used x-rays diffraction for diagnostic structure and nature thin film material. the results appear that the thin film is poly crystalline structure, the thermal annealing leads to drop of diffraction peaks and increase it edges that's means it become more uniformity as well as it consist of optical properties study about spectrum record for absorbance and transmission for the prepared thin films in visible region and ultraviolet for range of wave length 300-900 nm.



[1,2]

4.27 Å

monoclinic

p-type

[3,4] 2 eV

holes

:1

[5]

.13%

()

Cu₂O

[7,6]

10⁻²Torr

[6]

10⁻⁴ Torr

3*10⁻³ Torr

1

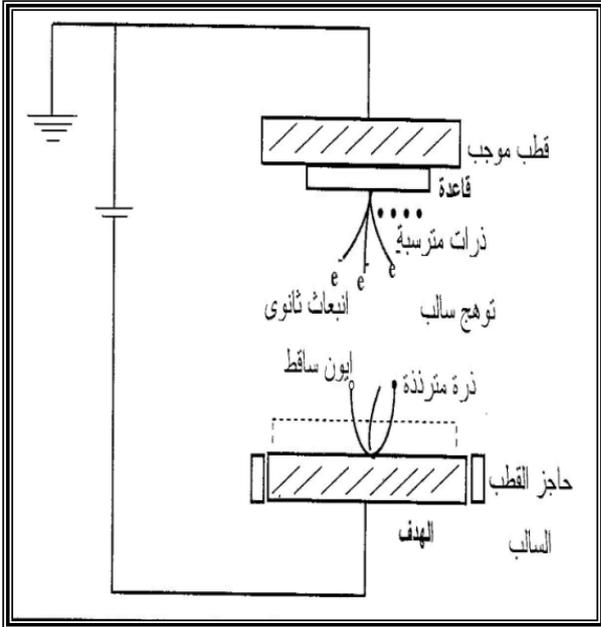
2

3

()



:2



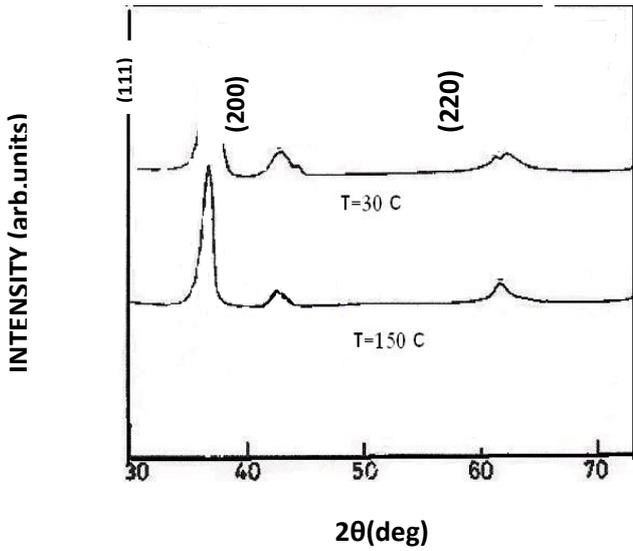
: 3 [8]

[7]

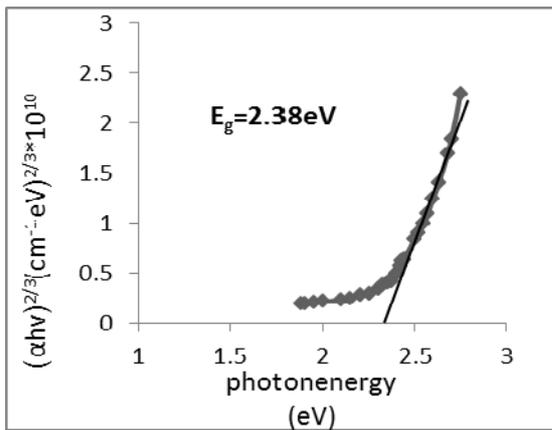
2000 Å
Cu₂O
150 °C

Cu ₂ O	Degree 2θ	d -value	hkl
	36.5	2.460	111
	42.40	2.130	200
	61.40	1.513	220
	36.8	2.463	111
	42.75	2.135	200
	61.60	1.519	220

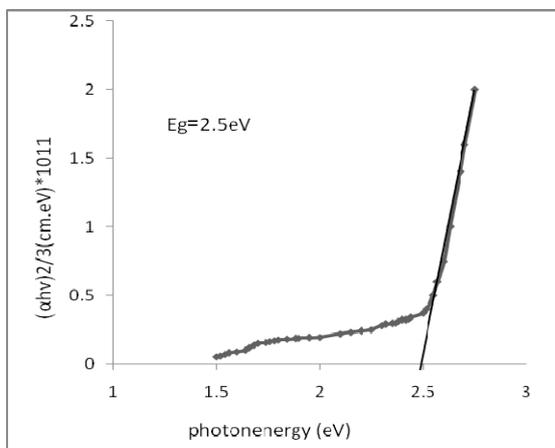
Cu₂O
150 °C
2000 Å
(POLY CRYSTALLAIN)
4
Cu₂O
Cu₂O
2000 Å
Cu₂O
(d-value)
(2d sin θ = nλ)
Cu₂O



Cu₂O :4



Cu₂O :5
2000Å



Cu₂O :6
150°C
2000Å

/ 300-900 nm
2000Å Cu₂O

(K_s) (α) (R) (n)

Cu₂O
: [8]

$$\alpha h\nu = B \{h\nu - E_g^{\text{opt}}\}^r \dots\dots (1)$$

: α
: B
: r
: hν
: E_g^{opt}

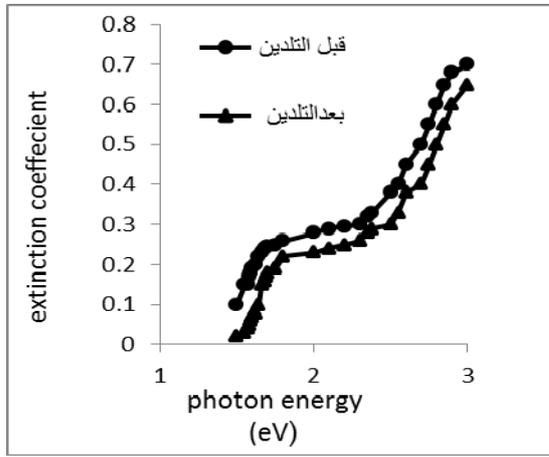
$$\frac{1}{2} \quad r$$

$$r = 3/2$$

$$(\alpha h\nu)^{2/3}$$

$$(\alpha h\nu)^{2/3} = 0$$

2000Å Cu₂O
E_g^{opt} = 2.38 eV
150°C
E_g = 2.5 eV



:8

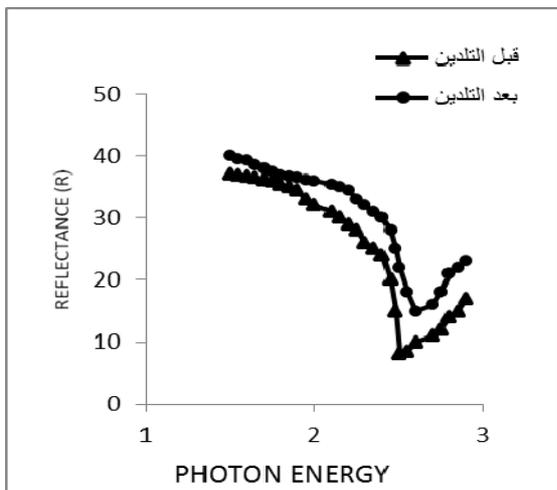
Cu₂O

(R)
Cu₂O
(T) (A)

: [10]

R=1-A-T(5)

9



Cu₂O

:9

(α)

: -

$\alpha = 2.303A/t$ (2)

:A

: t

: [9]

$h\nu = 1240/\lambda$ (3)

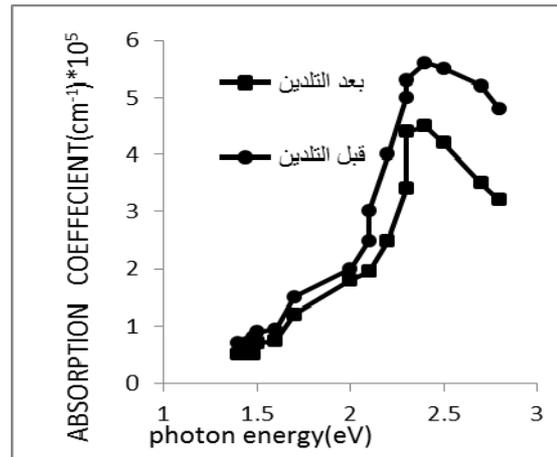
nm

eV

λ :

$h\nu$

150°C



:7

Cu₂O

(κ_o)

: -

Cu₂O

: [10]

$\kappa_o = \lambda\alpha/4\pi$ (4)

8

(n) :-

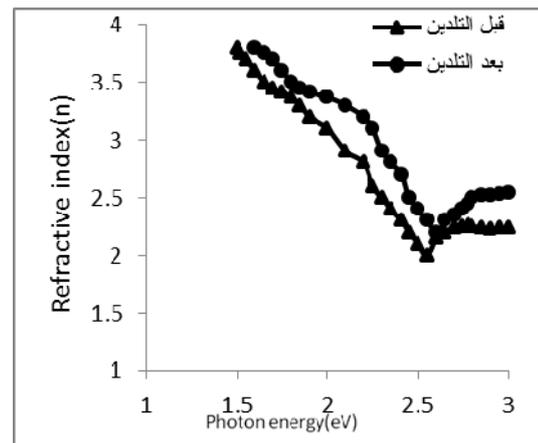
Cu₂O

: [11]

$$n = \left\{ \left(\frac{1+R}{1-R} \right)^2 - (K^2 + 1) \right\}^{1/2} + \left(\frac{1+R}{1-R} \right) \dots \dots (6)$$

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150°C

Cu₂O

:

Cu₂OCu₂O

°C

١٥٠°C

